

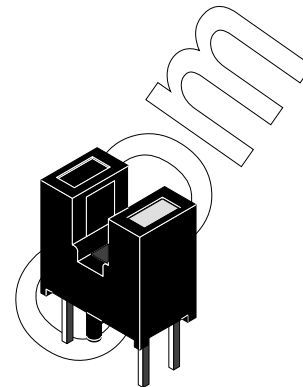
# Transmissive Optical Sensor with Phototransistor Output

## Description

This device has a compact construction where the emitting-light sources and the detectors are located face-to-face on the same optical axis. The operating wavelength is 950 nm. The detector consists of a phototransistor.

## Applications

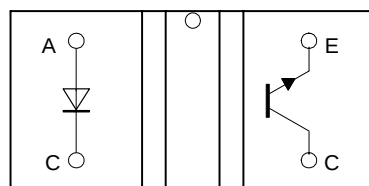
- Position sensor for shaft encoder
- Detection of opaque material such as paper, IBM cards, magnetic tapes etc.
- Limit switch for mechanical motions in VCR
- General purpose – wherever the space is limited
- End of tape, begin of tape in streamer



95 10529

## Features

- Gap 3 mm
- Package height: 8 mm
- Plastic polycarbonate housing
- Ambient light protected
- L = long leads
- Current Transfer Ratio (CTR) of typical 25%



96 11970

## Order Instruction

| Ordering Code | Resolution (mm) / Aperture (mm) | Remarks                                   |
|---------------|---------------------------------|-------------------------------------------|
| TCST1030      | / non                           | High density packing leads (3.4 mm)       |
| TCST1030(L)   | / non                           | High density packing long leads (16.2 mm) |

## Absolute Maximum Ratings

### Input (Emitter)

| Parameter             | Test Conditions           | Symbol    | Value | Unit       |
|-----------------------|---------------------------|-----------|-------|------------|
| Reverse voltage       |                           | $V_R$     | 6     | V          |
| Forward current       |                           | $I_F$     | 60    | mA         |
| Forward surge current | $t_p \leq 10 \mu s$       | $I_{FSM}$ | 3     | A          |
| Power dissipation     | $T_{amb} \leq 25^\circ C$ | $P_V$     | 100   | mW         |
| Junction temperature  |                           | $T_j$     | 100   | $^\circ C$ |

### Output (Detector)

| Parameter                 | Test Conditions           | Symbol    | Value | Unit       |
|---------------------------|---------------------------|-----------|-------|------------|
| Collector emitter voltage |                           | $V_{CEO}$ | 70    | V          |
| Emitter collector voltage |                           | $V_{ECO}$ | 7     | V          |
| Collector current         |                           | $I_C$     | 100   | mA         |
| Power dissipation         | $T_{amb} \leq 25^\circ C$ | $P_V$     | 150   | mW         |
| Junction temperature      |                           | $T_j$     | 100   | $^\circ C$ |

### Coupler

| Parameter                   | Test Conditions                 | Symbol    | Value       | Unit       |
|-----------------------------|---------------------------------|-----------|-------------|------------|
| Total power dissipation     | $T_{amb} \leq 25^\circ C$       | $P_{tot}$ | 250         | mW         |
| Operation temperature range |                                 | $T_{amb}$ | -25 to +85  | $^\circ C$ |
| Storage temperature range   |                                 | $T_{stg}$ | -25 to +100 | $^\circ C$ |
| Soldering temperature       | 1.6 mm from case, $t \leq 10 s$ | $T_{sd}$  | 260         | $^\circ C$ |

## Electrical Characteristics ( $T_{amb} = 25^\circ C$ )

### Input (Emitter)

| Parameter            | Test Conditions      | Symbol | Min. | Typ. | Max. | Unit |
|----------------------|----------------------|--------|------|------|------|------|
| Forward voltage      | $I_F = 60 mA$        | $V_F$  |      | 1.25 | 1.5  | V    |
| Junction capacitance | $V_R = 0, f = 1 MHz$ | $C_j$  |      | 50   |      | pF   |

### Output (Detector)

| Parameter                 | Test Conditions                 | Symbol    | Min. | Typ. | Max. | Unit |
|---------------------------|---------------------------------|-----------|------|------|------|------|
| Collector emitter voltage | $I_C = 1 mA$                    | $V_{CEO}$ | 70   |      |      | V    |
| Emitter collector voltage | $I_E = 10 \mu A$                | $V_{ECO}$ | 7    |      |      | V    |
| Collector dark current    | $V_{CE} = 25 V, I_F = 0, E = 0$ | $I_{CEO}$ |      | 10   | 100  | nA   |

### Coupler

| Parameter                            | Test Conditions             | Symbol      | Min. | Typ. | Max. | Unit |
|--------------------------------------|-----------------------------|-------------|------|------|------|------|
| Collector current                    | $V_{CE} = 5 V, I_F = 10 mA$ | $I_C$       | 1.2  | 2.4  |      | mA   |
| Collector emitter saturation voltage | $I_F = 10 mA, I_C = 1 mA$   | $V_{CEsat}$ |      |      | 0.8  | V    |

## Switching Characteristics

| Parameter     | Test Conditions                                                                   | Symbol    | Typ. | Unit          |
|---------------|-----------------------------------------------------------------------------------|-----------|------|---------------|
| Turn-on time  | $I_C = 1 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ , $R_L = 100 \Omega$ (see figure 1) | $t_{on}$  | 15.0 | $\mu\text{s}$ |
| Turn-off time |                                                                                   | $t_{off}$ | 10.0 | $\mu\text{s}$ |

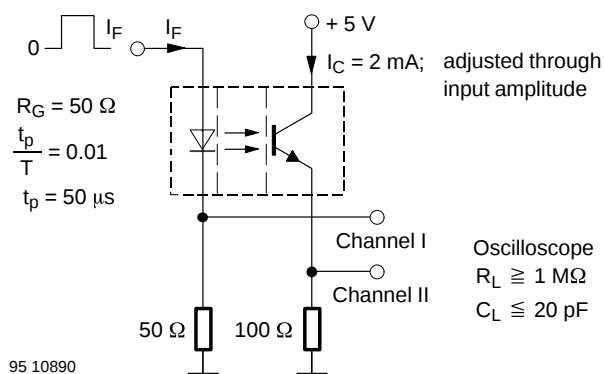


Figure 1. Test circuit

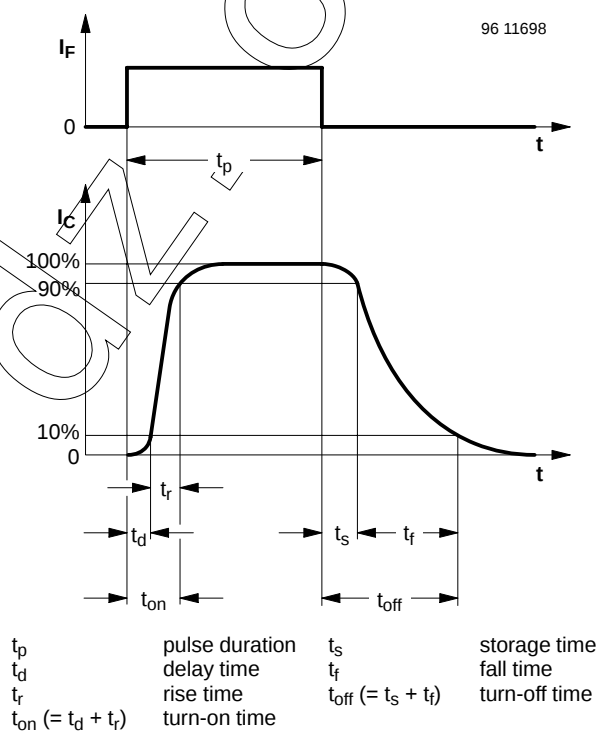


Figure 2. Switching times

## Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ , unless otherwise specified)

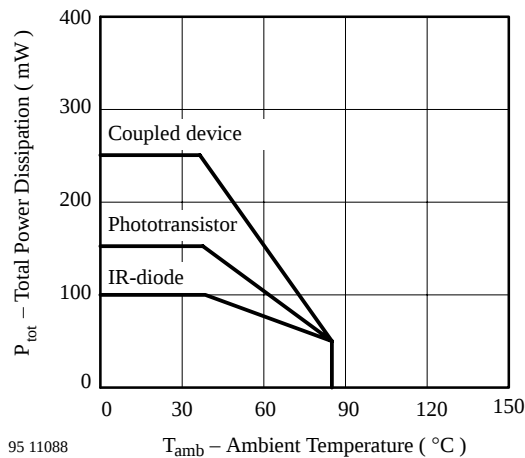


Figure 3. Total Power Dissipation vs. Ambient Temperature

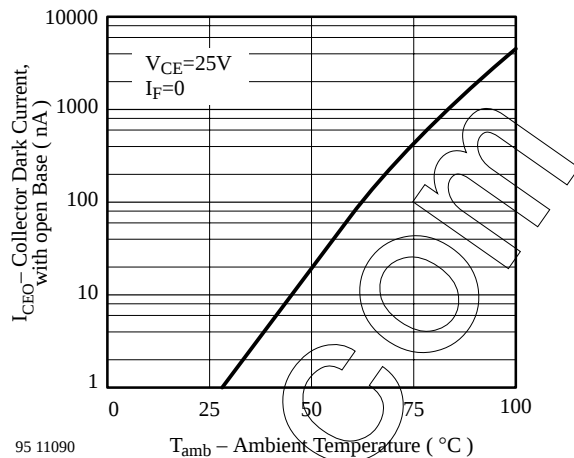


Figure 6. Collector Dark Current vs. Ambient Temperature

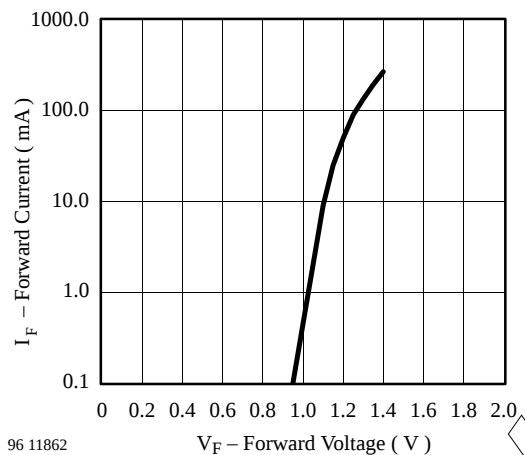


Figure 4. Forward Current vs. Forward Voltage

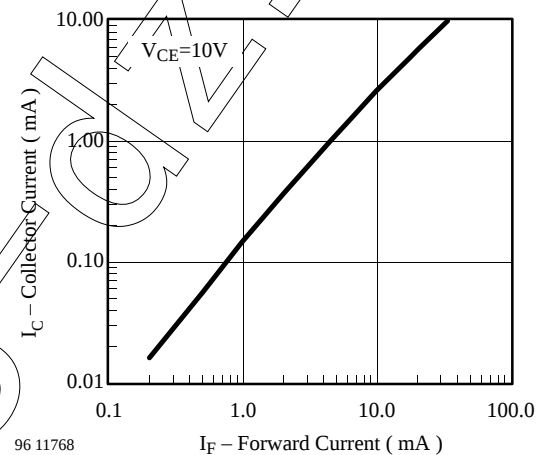


Figure 7. Collector Current vs. Forward Current

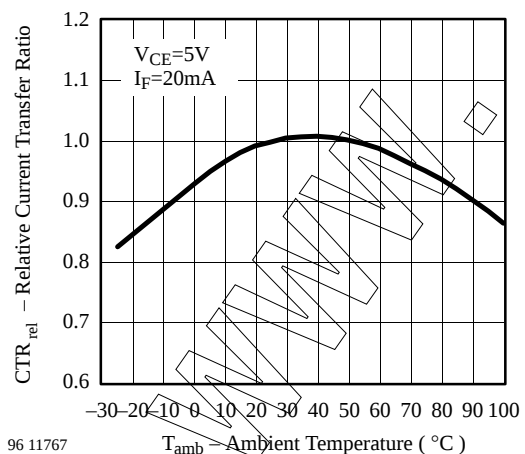


Figure 5. Relative Current Transfer Ratio vs. Ambient Temperature

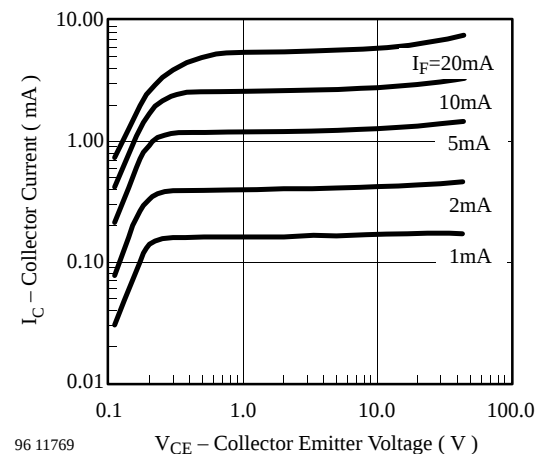


Figure 8. Collector Current vs. Collector Emitter Voltage

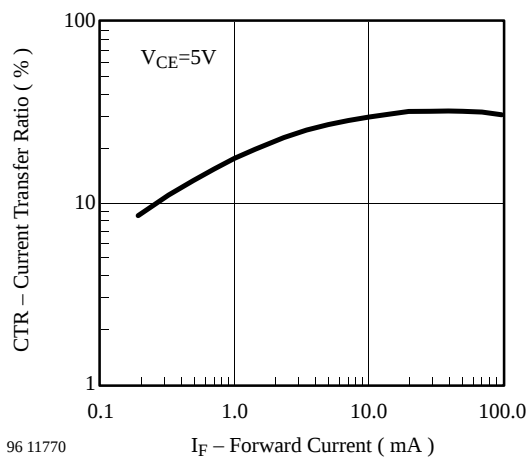


Figure 9. Current Transfer Ratio vs. Forward Current

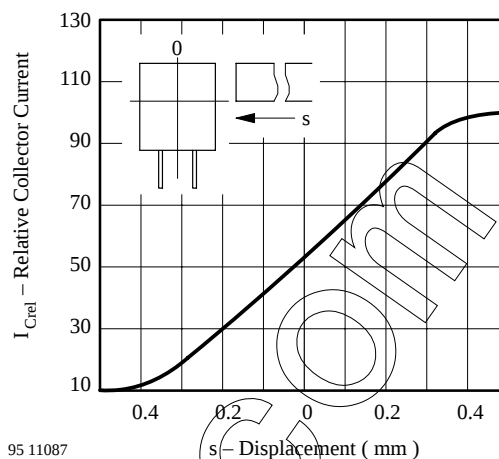


Figure 11. Relative Collector Current vs. Displacement

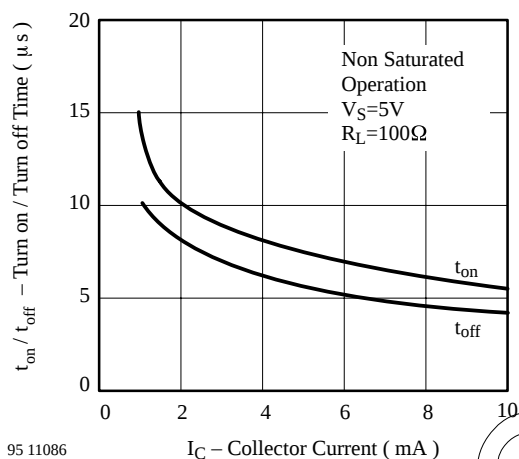


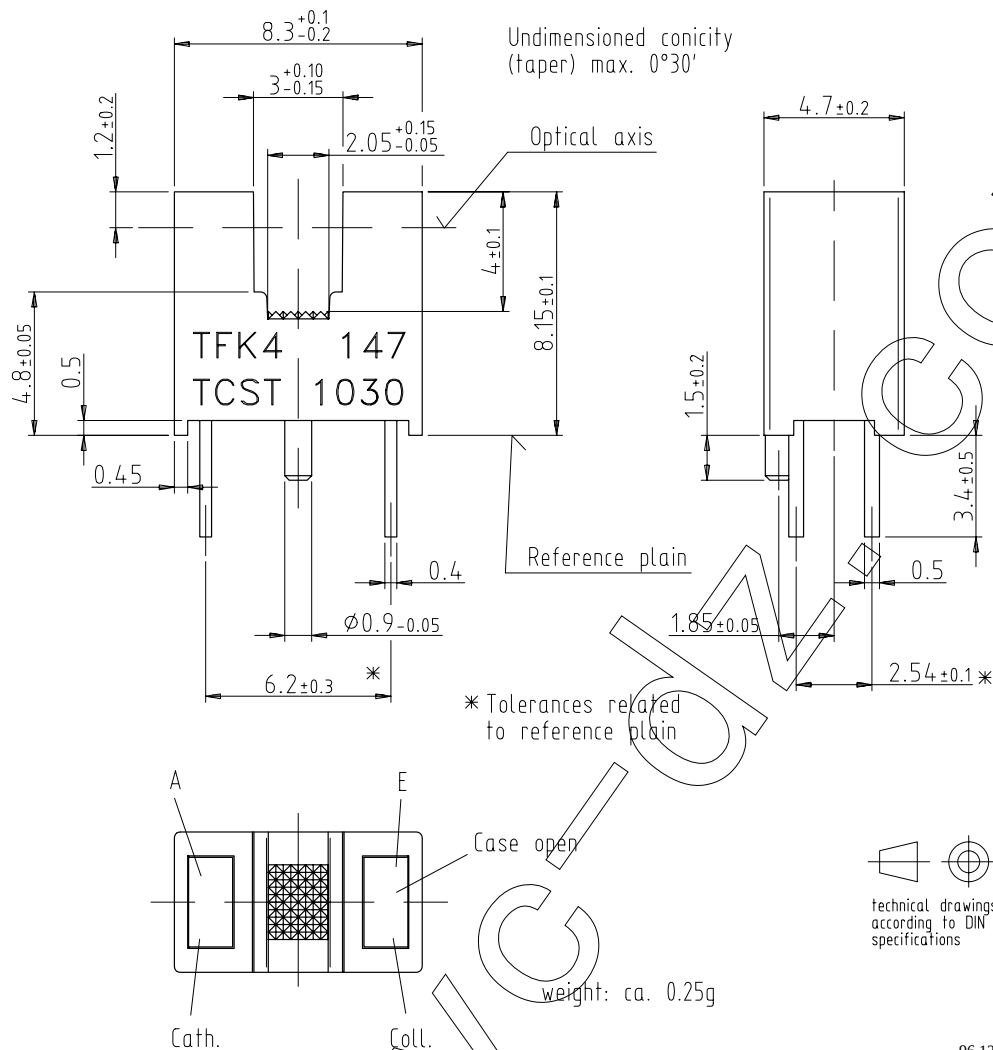
Figure 10. Turn on / off Time vs. Collector Current

# TCST1030(L)

Vishay Semiconductors

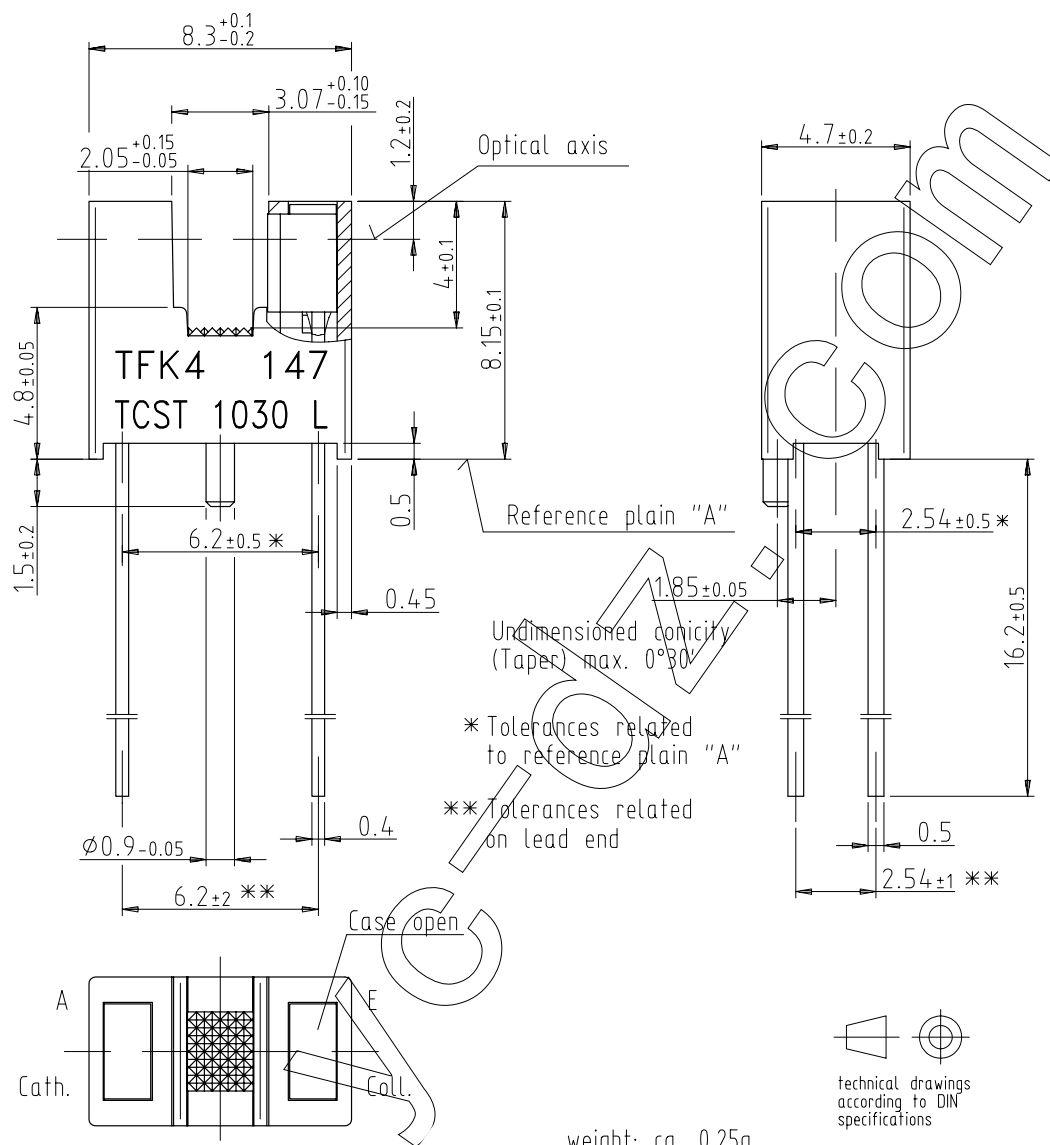


## Dimensions of TCST1030 in mm



96 12074

### Dimensions of TCST1030L in mm



Drawing-No.: 6.550-5147.01-4  
Issue: 2; 10.11.98

95 11268



### Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany  
Telephone: 49 (0) 7131 67 2831, Fax number: 49 (0) 7131 67 2423